



An IXYS Company

Date:- 2<sup>nd</sup> Mar, 2009

Data Sheet Issue:- 1

# Medium Voltage Thyristor

## Type K0885N#440 to K0885N#520

Development Part No.: Kx193NC440-520

### Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V <sub>DRM</sub>	Repetitive peak off-state voltage, (note 1)	4400-5200	V
V <sub>DSM</sub>	Non-repetitive peak off-state voltage, (note 1)	4400-5200	V
V <sub>RRM</sub>	Repetitive peak reverse voltage, (note 1)	4400-5200	V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage, (note 1)	4500-5300	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I <sub>T(AV)M</sub>	Maximum average on-state current, T <sub>sink</sub> =55°C, (note 2)	885	A
I <sub>T(AV)M</sub>	Maximum average on-state current. T <sub>sink</sub> =85°C, (note 2)	620	A
I <sub>T(AV)M</sub>	Maximum average on-state current. T <sub>sink</sub> =85°C, (note 3)	387	A
I <sub>T(RMS)</sub>	Nominal RMS on-state current, T <sub>sink</sub> =25°C, (note 2)	1728	A
I <sub>T(d.c.)</sub>	D.C. on-state current, T <sub>sink</sub> =25°C, (note 4)	1544	A
I <sub>TSM</sub>	Peak non-repetitive surge t <sub>p</sub> =10ms, V <sub>rm</sub> =60%V <sub>RRM</sub> , (note 5)	10000	A
I <sub>TSM2</sub>	Peak non-repetitive surge t <sub>p</sub> =10ms, V <sub>rm</sub> ≤10V, (note 5)	11000	A
I <sup>2</sup> t	I <sup>2</sup> t capacity for fusing t <sub>p</sub> =10ms, V <sub>rm</sub> =60%V <sub>RRM</sub> , (note 5)	500×10 <sup>3</sup>	A <sup>2</sup> s
I <sup>2</sup> t	I <sup>2</sup> t capacity for fusing t <sub>p</sub> =10ms, V <sub>rm</sub> ≤10V, (note 5)	605×10 <sup>3</sup>	A <sup>2</sup> s
(di/dt) <sub>cr</sub>	Critical rate of rise of on-state current (Note 6)	continuous, 50Hz repetitive, 50Hz, 60s non-repetitive	150 300 600 A/μs
V <sub>RGM</sub>	Peak reverse gate voltage	5	V
P <sub>G(AV)</sub>	Mean forward gate power	2	W
P <sub>GM</sub>	Peak forward gate power	30	W
T <sub>j op</sub>	Operating temperature range	-40 to +125	°C
T <sub>stg</sub>	Storage temperature range	-40 to +150	°C

Notes:-

- De-rating factor of 0.13% per °C is applicable for T<sub>j</sub> below 25°C.
- Double side cooled, single phase; 50Hz, 180° half-sinewave.
- Single side cooled, single phase; 50Hz, 180° half-sinewave.
- Double side cooled.
- Half-sinewave, 125°C T<sub>j</sub> initial.
- V<sub>D</sub>=67% V<sub>DRM</sub>, I<sub>FG</sub>=2A, t<sub>r</sub>≤0.5μs, T<sub>case</sub>=125°C.

**Characteristics**

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V <sub>TM</sub>	Maximum peak on-state voltage	-	-	2.20	I <sub>TM</sub> =1000A,	V
V <sub>TM</sub>	Maximum peak on-state voltage	-	-	3.74	I <sub>TM</sub> =2660A	V
V <sub>T0</sub>	Threshold voltage	-	-	1.27		V
r <sub>T</sub>	Slope resistance	-	-	0.93		mΩ
(dv/dt) <sub>cr</sub>	Critical rate of rise of off-state voltage	1000	-	-	V <sub>D</sub> = V, linear ramp, gate o/c	V/μs
I <sub>DRM</sub>	Peak off-state current	-	-	50	Rated V <sub>DRM</sub>	mA
I <sub>RRM</sub>	Peak reverse current	-	-	50	Rated V <sub>RRM</sub>	mA
V <sub>GT</sub>	Gate trigger voltage	-	-	3.0	T <sub>J</sub> =25°C V <sub>D</sub> =10V, I <sub>T</sub> =3A	V
I <sub>GT</sub>	Gate trigger current	-	-	300		mA
V <sub>GD</sub>	Gate non-trigger voltage	-	-	0.25	Rated V <sub>DRM</sub>	V
I <sub>H</sub>	Holding current	-	-	1000	T <sub>J</sub> =25°C	mA
t <sub>gd</sub>	Gate-controlled turn-on delay time	-	0.4	1.0	V <sub>D</sub> = 50% V <sub>DRM</sub> , I <sub>TM</sub> =1000A, di/dt=10A/μs,	μs
t <sub>gt</sub>	Turn-on time	-	1.2	1.8	I <sub>FG</sub> =2A, t <sub>r</sub> =0.5μs, T <sub>J</sub> =25°C	μs
Q <sub>rr</sub>	Recovered charge	-	5300	6000		μC
Q <sub>ra</sub>	Recovered charge, 50% Chord	-	2300	-	I <sub>TM</sub> =1000A, t <sub>p</sub> =1000μs, di/dt=10A/μs,	μC
I <sub>rm</sub>	Reverse recovery current	-	150	-	V <sub>r</sub> =50V	A
t <sub>rr</sub>	Reverse recovery time, 50% Chord	-	30	-		μs
t <sub>q</sub>	Turn-off time	-	700	-	I <sub>TM</sub> =1000A, t <sub>p</sub> =1000μs, di/dt=10A/μs, V <sub>r</sub> =50V, V <sub>dr</sub> =33%V <sub>DRM</sub> , dV <sub>dr</sub> /dt=20V/μs	μs
		-	1000	-	I <sub>TM</sub> =1000A, t <sub>p</sub> =1000μs, di/dt=10A/μs, V <sub>r</sub> =50V, V <sub>dr</sub> =33%V <sub>DRM</sub> , dV <sub>dr</sub> /dt=200V/μs	
R <sub>thJK</sub>	Thermal resistance, junction to heatsink	-	-	0.024	Double side cooled	K/W
		-	-	0.048	Single side cooled	K/W
F	Mounting force	19	-	26	(Note 2)	kN
W <sub>t</sub>	Weight	-	500	-	Outline option NC	g
		-	500	-	Outline option NG	

Notes:-

- 1) Unless otherwise indicated T<sub>J</sub>=125°C.
- 2) For other mounting forces, please consult factory.

**Notes on Ratings and Characteristics****1.0 Voltage Grade Table**

Voltage Grade	$V_{DRM}$ $V_{DSM}$ $V_{RRM}$ V	$V_{RSM}$ V	$V_D/V_R$ DC V
44	4400	4500	2080
48	4800	4900	2160
50	5000	5100	2200
52	5200	5300	2240

**2.0 Extension of Voltage Grades**

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

**3.0 De-rating Factor**

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for  $T_j$  below 25°C.

**4.0 Repetitive dv/dt**

Standard dv/dt is 1000V/μs.

**5.0 Frequency Ratings**

The curves illustrated in figures 16 & 17 are for guidance only and are superseded by the maximum ratings shown on page 1. For operation above line frequency, please consult the factory for assistance.

**6.0 Snubber Components**

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

**7.0 Rate of rise of on-state current**

The maximum un-primed rate of rise of on-state current must not exceed 600A/μs at any time during turn-on on a non-repetitive basis. For repetitive performance, the on-state rate of rise of current must not exceed 300A/μs at any time during turn-on. Note that these values of rate of rise of current apply to the total device current including that from any local snubber network.

**8.0 Square wave frequency ratings**

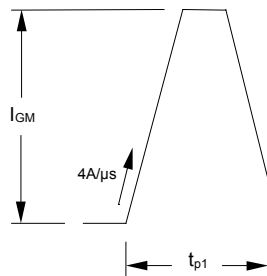
These ratings are given for load component rate of rise of on-state current of 100A/μs.

**9.0 Duty cycle lines**

The 100% duty cycle is represented on the frequency ratings by a straight line. Other duties can be included as parallel to the first.

**10.0 Gate Drive**

The nominal requirement for a typical gate drive is illustrated below. An open circuit voltage of at least 30V is assumed. This gate drive must be applied when using the full di/dt capability of the device.



The magnitude of  $I_{GM}$  should be between five and ten times  $I_{GT}$ , which is shown on page 2. Its duration ( $t_{p1}$ ) should be 20μs or sufficient to allow the anode current to reach ten times  $I_L$ , whichever is greater. Otherwise, an increase in pulse current could be needed to supply the necessary charge to trigger. The 'back-porch' current  $I_G$  should remain flowing for the same duration as the anode current and have a magnitude in the order of 1.5 times  $I_{GT}$ .

**11.0 Computer Modelling Parameters**

**11.1 Device Dissipation Calculations**

$$I_{AV} = \frac{-V_0 + \sqrt{V_0^2 + 4 \cdot ff \cdot r_s \cdot W_{AV}}}{2 \cdot ff \cdot r_s}$$

and:

$$W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j\max} - T_{Hs}$$

Where  $V_0=1.27V$ ,  $r_s=0.93m\Omega$ ,

$R_{th}$  = Supplementary thermal impedance, see table below and

$ff$  = Form factor, see table below.

**Supplementary Thermal Impedance**

Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave Double Side Cooled	0.0293	0.0285	0.0278	0.0271	0.0261	0.0249	0.024
Square wave Single Side Cooled	0.0534	0.053	0.0524	0.0518	0.0509	0.0497	0.048
Sine wave Double Side Cooled	0.0286	0.0276	0.0269	0.0263	0.0248		
Sine wave Single Side Cooled	0.0531	0.0523	0.0517	0.0511	0.0497		

**Form Factors**

Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.464	2.449	2	1.732	1.414	1.149	1
Sine wave	3.98	2.778	2.22	1.879	1.57		

11.2 Calculating  $V_T$  using ABCD Coefficients

The on-state characteristic  $I_T$  vs.  $V_T$ , on page 6 is represented in two ways;

- (i) the well established  $V_0$  and  $r_s$  tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for  $V_T$  in terms of  $I_T$  given below:

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for  $V_T$  agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		125°C Coefficients	
A	1.817265	A	0.1339075
B	-0.137011	B	0.1991792
C	4.436071e <sup>-4</sup>	C	8.79778e <sup>-4</sup>
D	0.0205661	D	-5.972062e <sup>-3</sup>

11.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \left( 1 - e^{-\frac{t}{\tau_p}} \right)$$

Where  $p = 1$  to  $n$ ,  $n$  is the number of terms in the series and.

- $t$  = Duration of heating pulse in seconds.
- $r_t$  = Thermal resistance at time  $t$ .
- $r_p$  = Amplitude of  $p_{th}$  term.
- $\tau_p$  = Time Constant of  $r_{th}$  term.

The coefficients for this device are shown in the tables below:

D.C. Double Side Cooled					
Term	1	2	3	4	5
$r_p$	0.01249139	6.316833×10 <sup>-3</sup>	1.850855×10 <sup>-3</sup>	1.922045×10 <sup>-3</sup>	6.135330×10 <sup>-4</sup>
$\tau_p$	0.8840810	0.1215195	0.03400152	6.742908×10 <sup>-3</sup>	1.326292×10 <sup>-3</sup>

D.C. Single Side Cooled						
Term	1	2	3	4	5	6
$r_p$	0.02919832	4.863568×10 <sup>-3</sup>	3.744798×10 <sup>-3</sup>	6.818034×10 <sup>-3</sup>	2.183558×10 <sup>-3</sup>	1.848294×10 <sup>-3</sup>
$\tau_p$	6.298105	3.286174	0.5359179	0.1186897	0.02404574	3.379476×10 <sup>-3</sup>

Curves

Figure 1 – On-state characteristics of Limit device

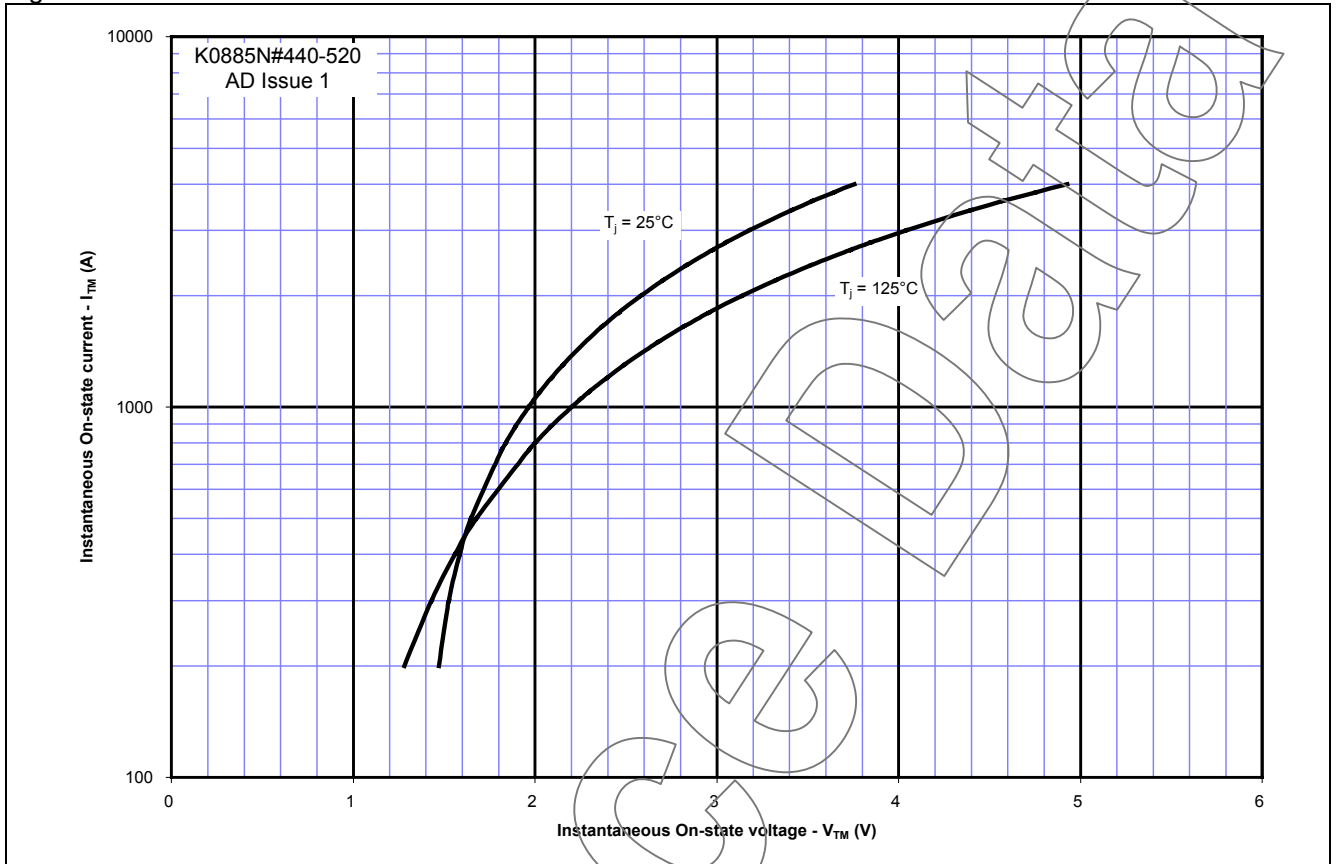


Figure 2 – Gate characteristics - Trigger limits

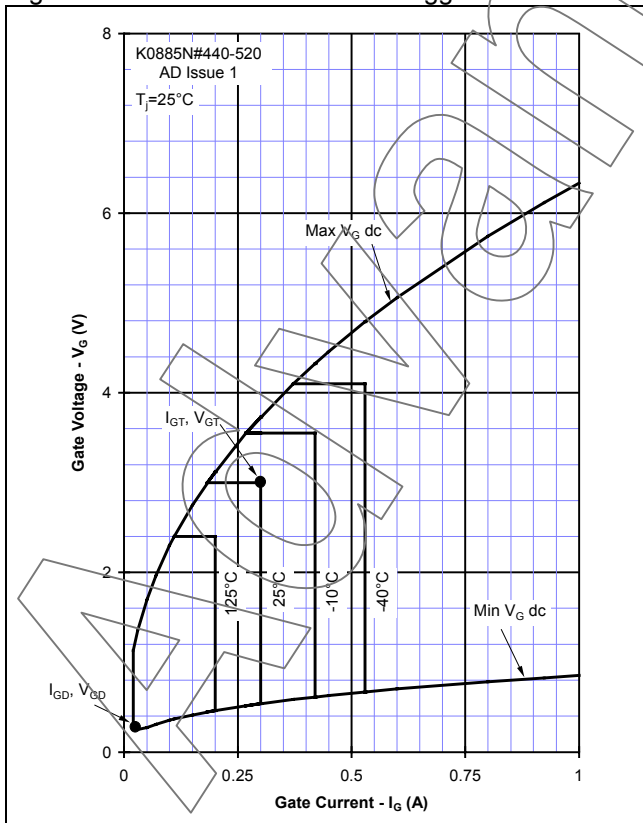


Figure 3 – Gate characteristics - Power curves

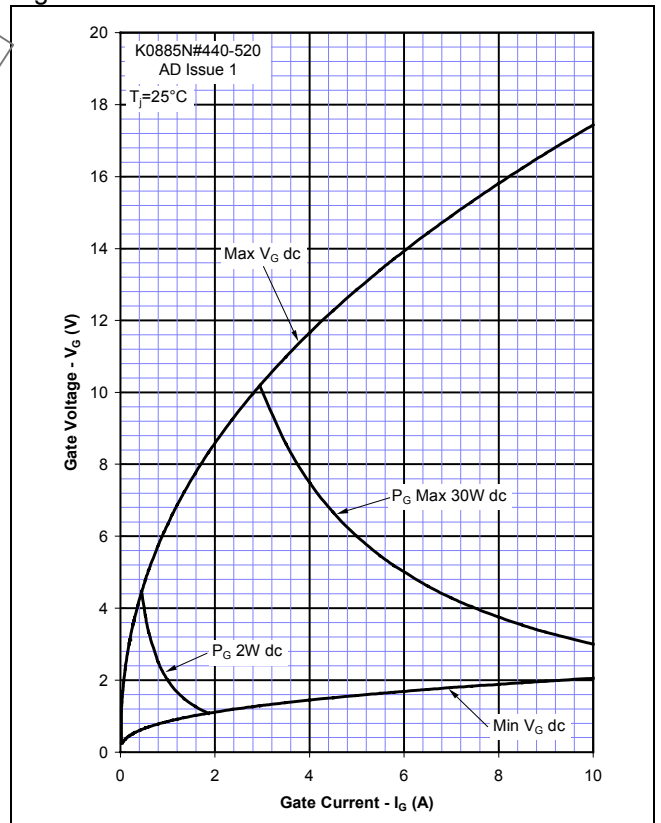


Figure 4 – Total recovered charge,  $Q_{rr}$

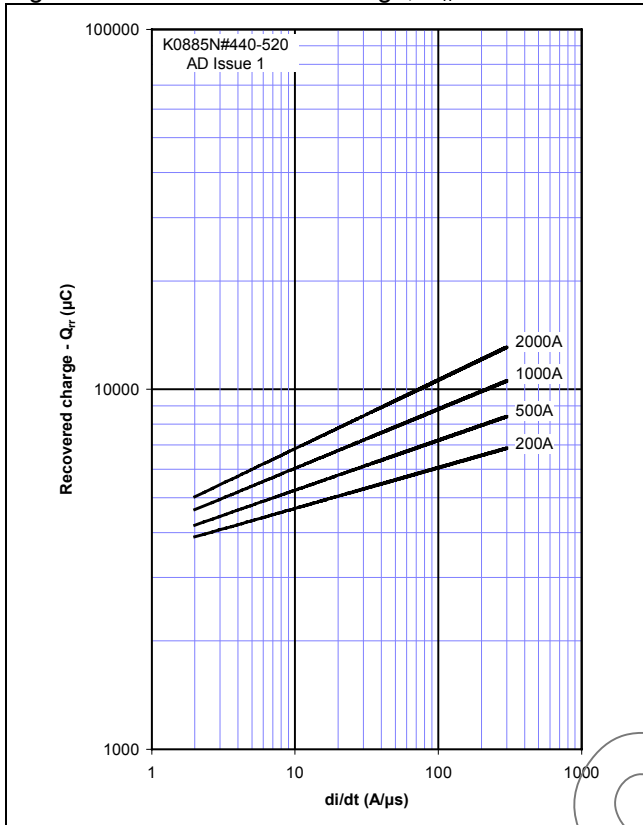


Figure 5 – Recovered charge,  $Q_{ra}$  (50% chord)

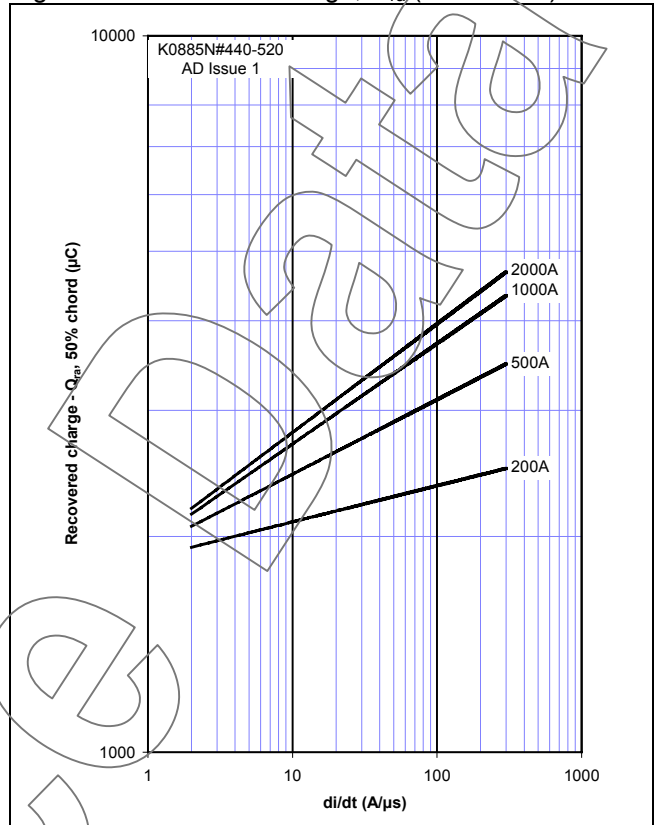


Figure 6 – Peak reverse recovery current,  $I_{rm}$

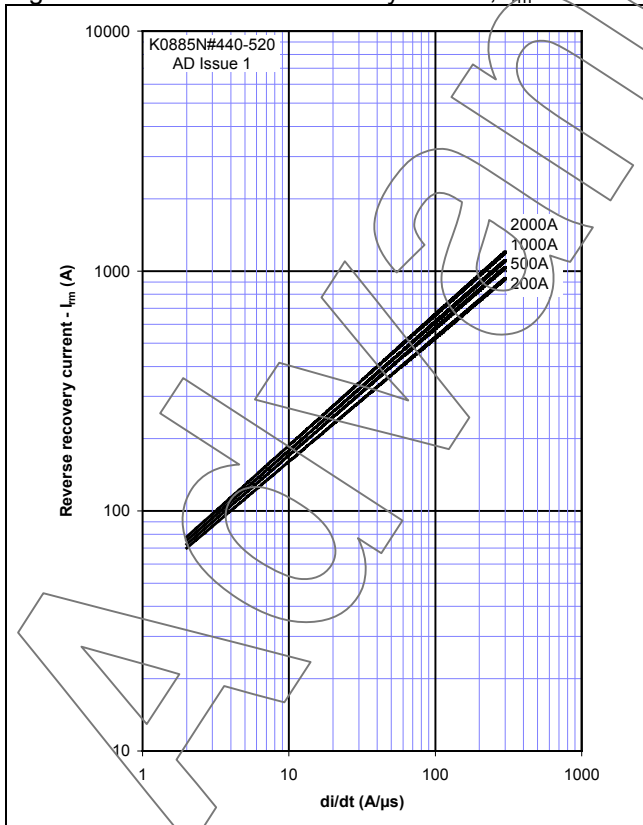


Figure 7 – Maximum recovery time,  $t_{rr}$  (50% chord)

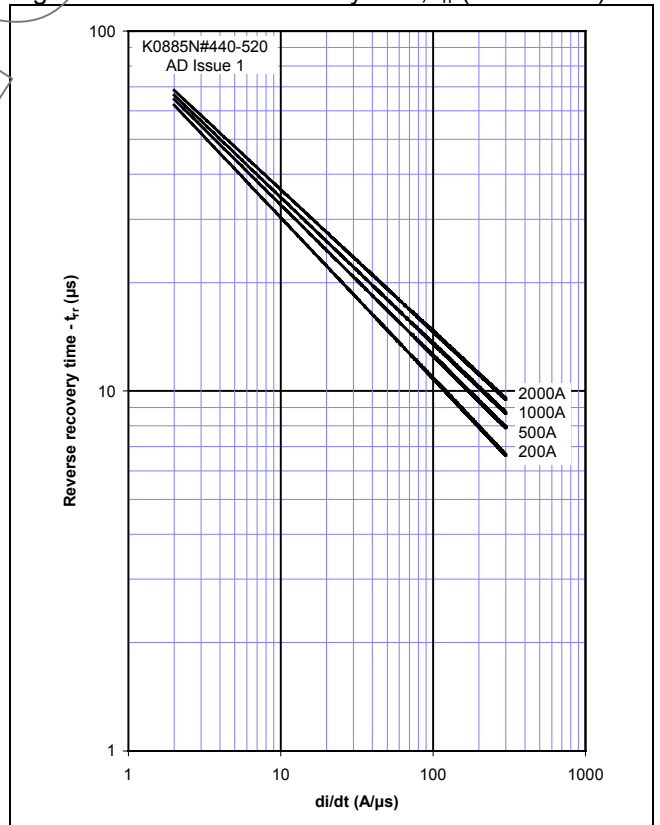


Figure 8 – On-state current vs. Power dissipation – Double Side Cooled (Sine wave)

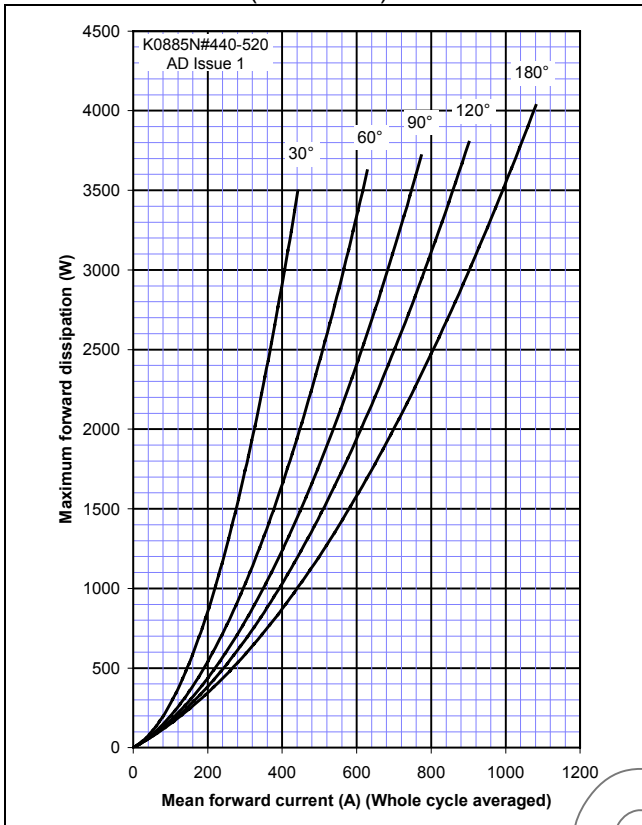


Figure 9 – On-state current vs. Heatsink temperature – Double Side Cooled (Sine wave)

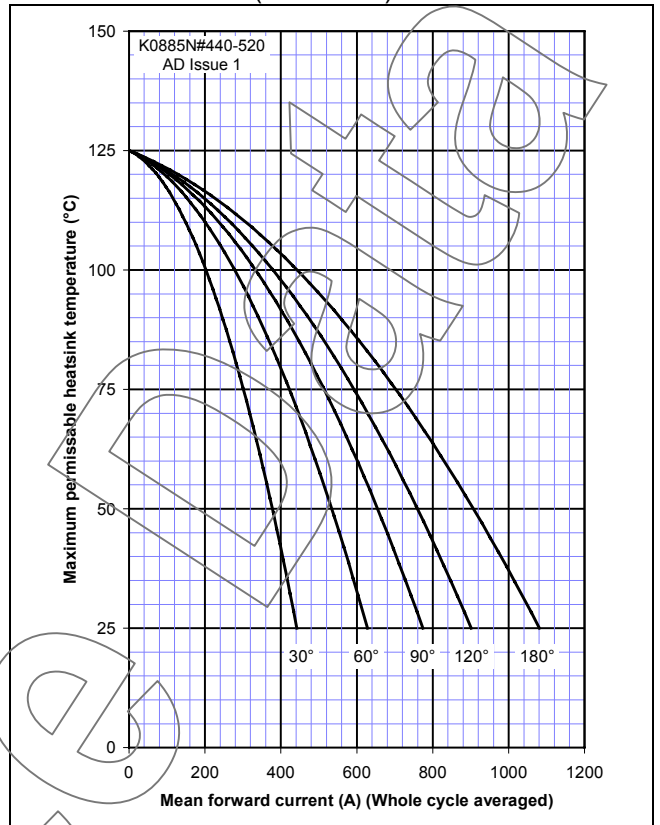


Figure 10 – On-state current vs. Power dissipation – Double Side Cooled (Square wave)

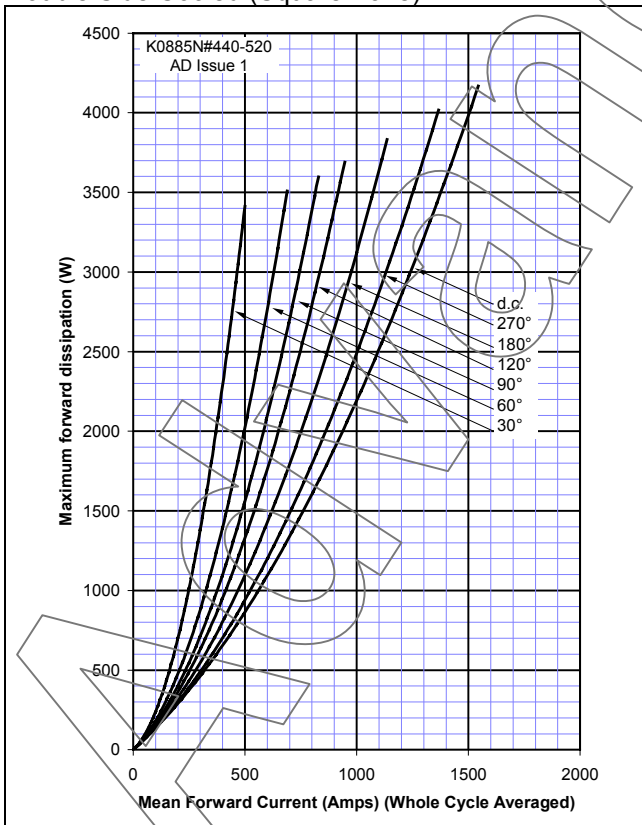


Figure 11 – On-state current vs. Heatsink temperature – Double Side Cooled (Square wave)

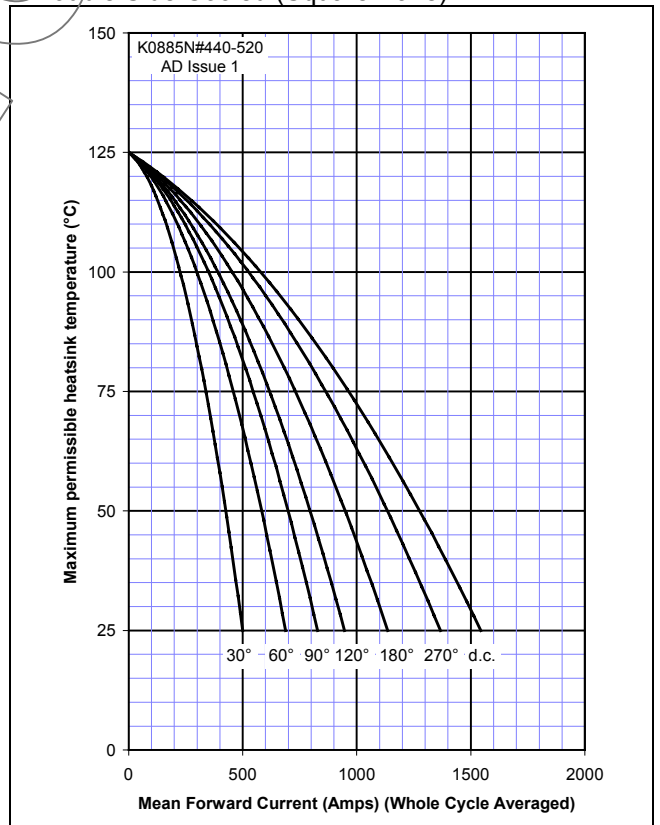




Figure 12 – On-state current vs. Power dissipation – Single Side Cooled (Sine wave)

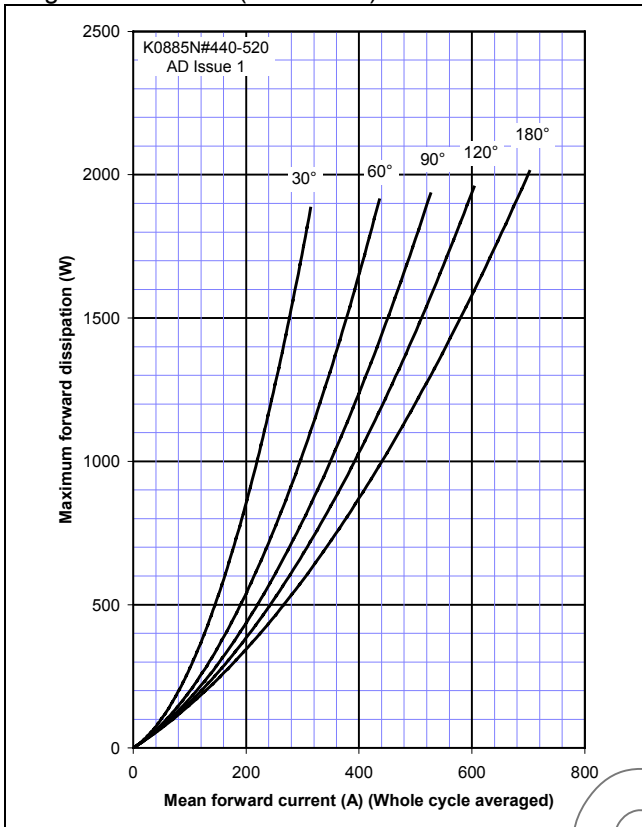


Figure 13 – On-state current vs. Heatsink temperature – Single Side Cooled (Sine wave)

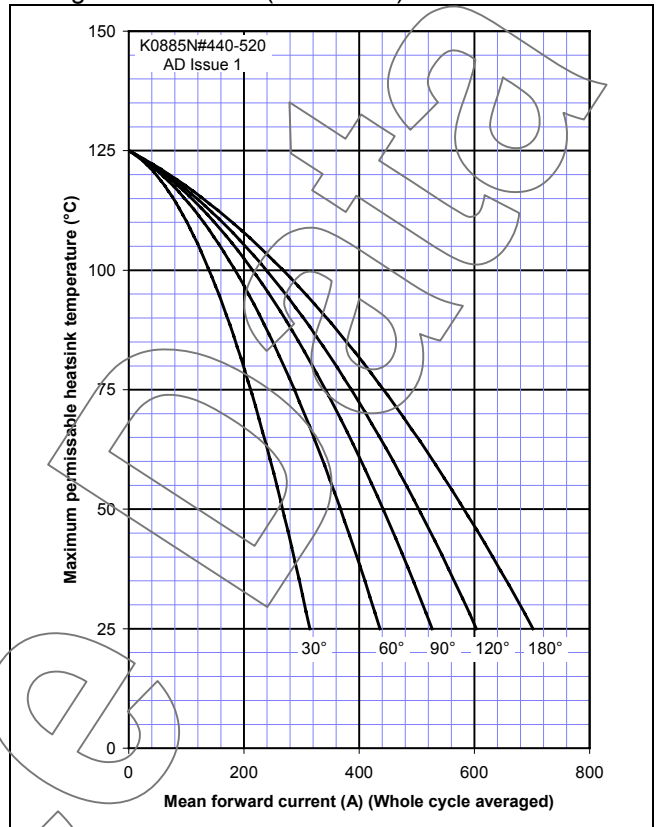


Figure 14 – On-state current vs. Power dissipation – Single Side Cooled (Square wave)

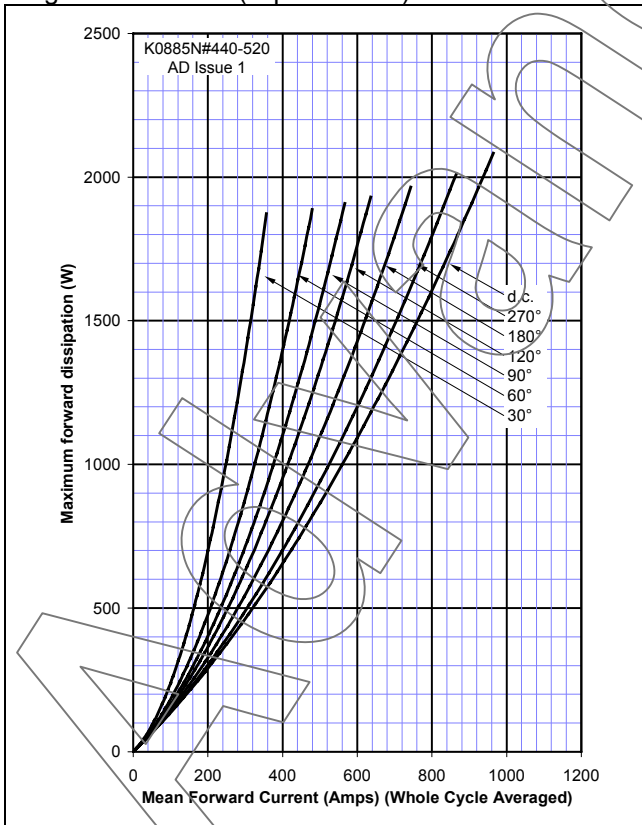


Figure 15 – On-state current vs. Heatsink temperature – Single Side Cooled (Square wave)

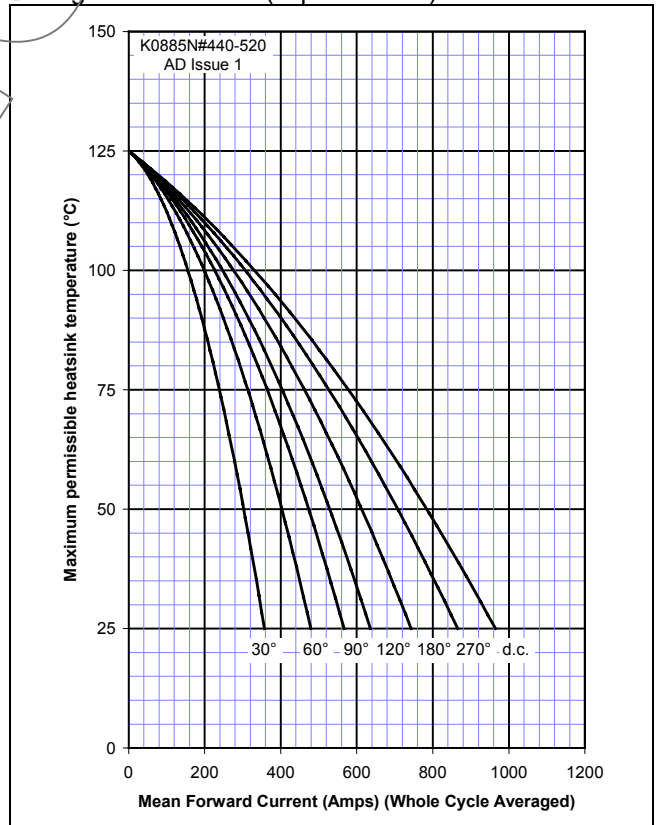


Figure 16 – Square wave frequency ratings

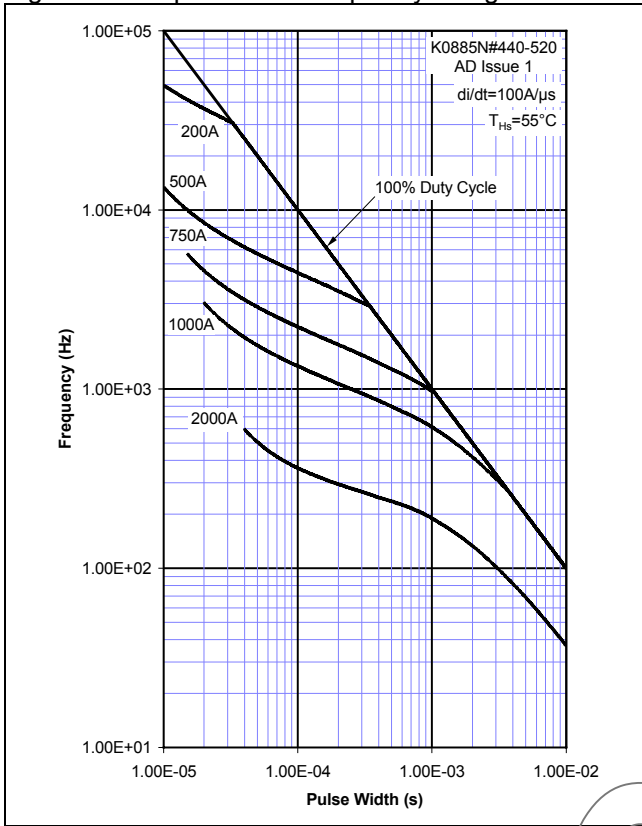


Figure 17 – Sine wave frequency ratings

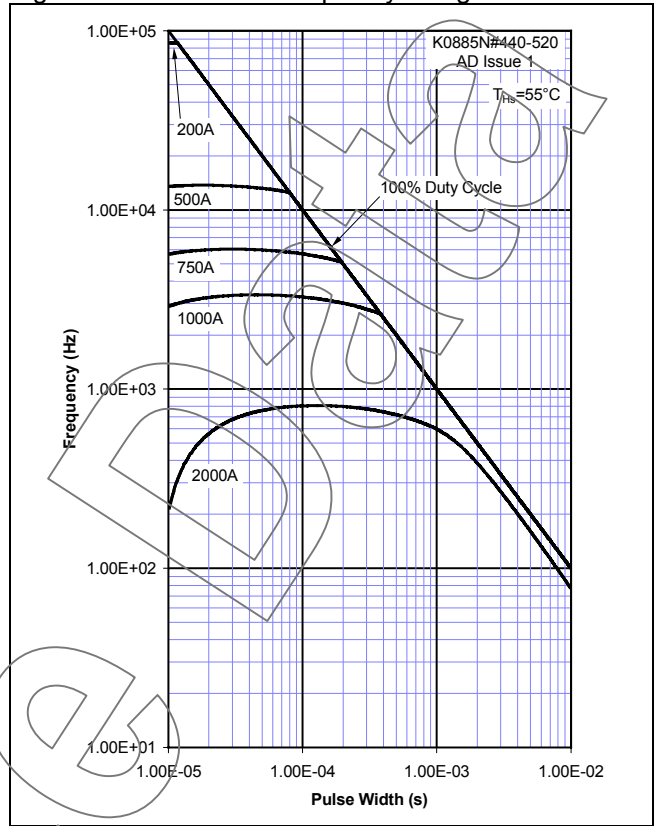


Figure 18 – Transient thermal impedance

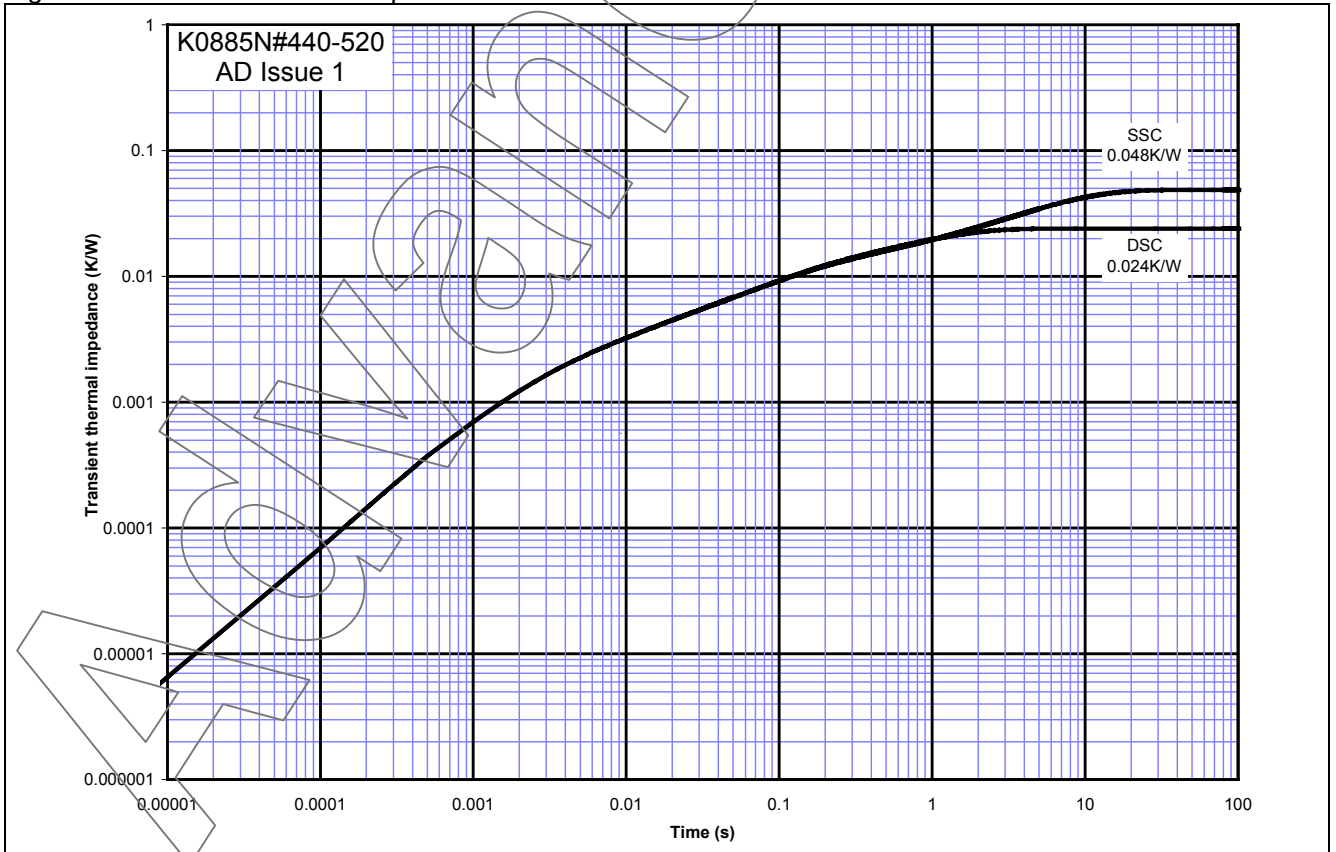
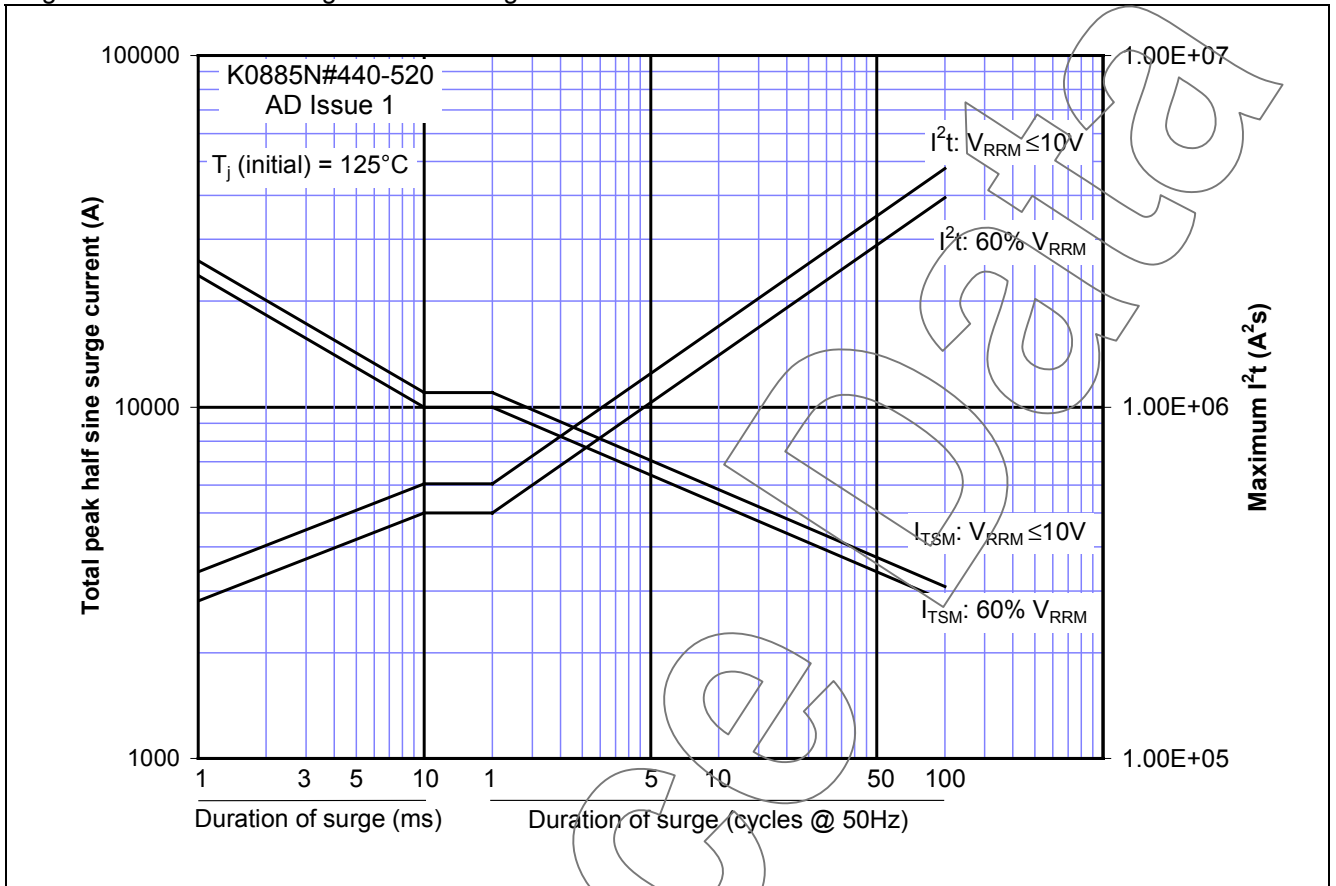
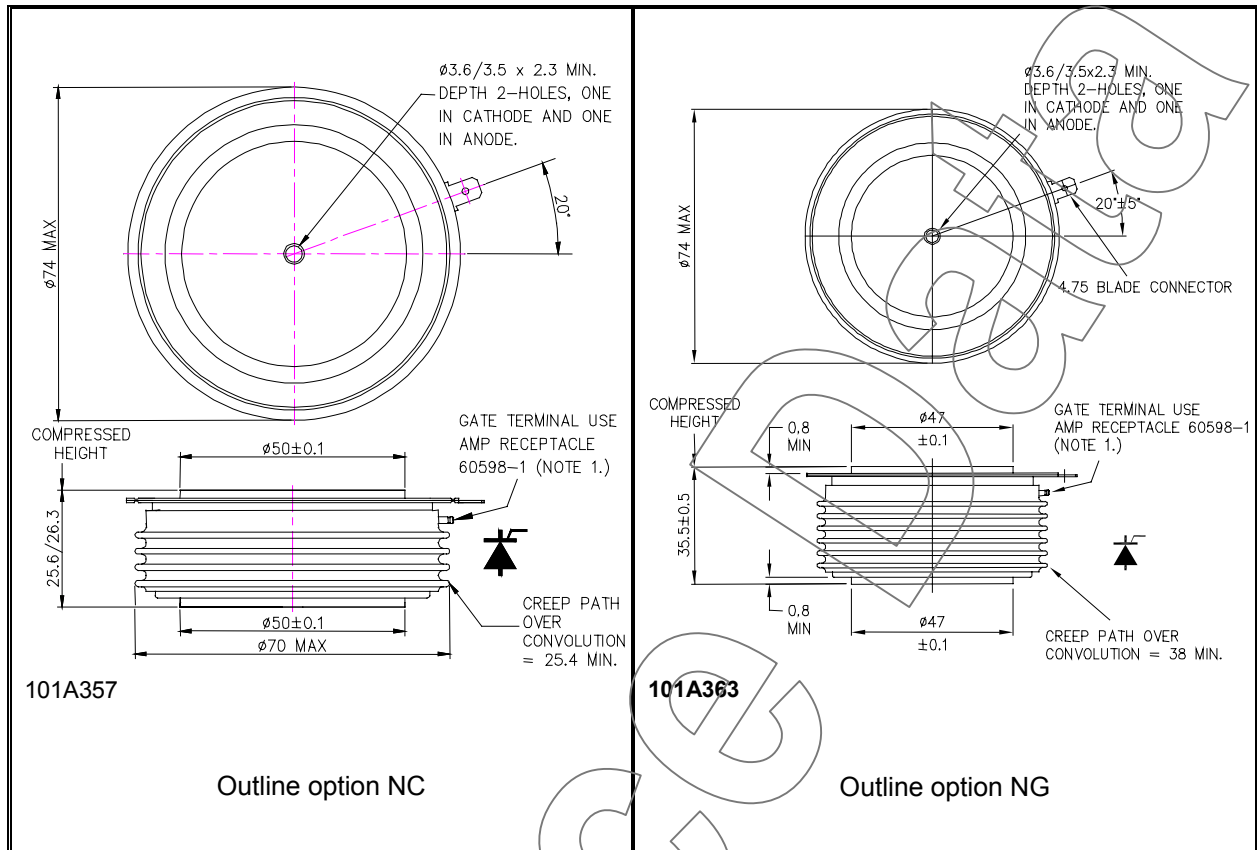


Figure 19 – Maximum surge and  $I^2t$  Ratings



**Outline Drawing & Ordering Information**



**ORDERING INFORMATION**

(Please quote 10 digit code as below)

<b>K0885</b>	<b>N#</b>	<b>◆◆</b>	<b>0</b>
Fixed type code	Outline code NC=27.7mm height NG=35.5mm height	Voltage code V <sub>DRM</sub> /100 44-52	Fixed turn-off time code

Order code: K0885NC520 – 5200V V<sub>DRM</sub>, V<sub>RRM</sub>; 26mm clamp height capsule.

**IXYS Semiconductor GmbH**  
Edisonstraße 15  
D-68623 Lampertheim  
Tel: +49 6206 503-0  
Fax: +49 6206 503-627  
E-mail: [marcom@ixys.de](mailto:marcom@ixys.de)

**WESTCODE**  
An IXYS Company

**Westcode Semiconductors Ltd**  
Langley Park Way, Langley Park,  
Chippenham, Wiltshire, SN15 1GE.  
Tel: +44 (0)1249 444524  
Fax: +44 (0)1249 659448  
E-mail: [WSL.sales@westcode.com](mailto:WSL.sales@westcode.com)

**IXYS Corporation**  
1590 Buckeye Drive  
Milpitas CA 95035 7418 USA  
Tel: +1 (408) 547 9000  
Fax: +1 (408) 496 0670  
E-mail: [sales@ixys.net](mailto:sales@ixys.net)

[www.westcode.com](http://www.westcode.com)

[www.ixys.com](http://www.ixys.com)

**IXYS Long Beach**  
2500 Mira Mar Avenue  
Long Beach CA 90815 USA  
Tel: +1 (562) 296-6584  
Fax: +1 (562) 296-6585  
E-mail: [WSI.sales@westcode.com](mailto:WSI.sales@westcode.com)

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